

[0075] Next, the manufacturer metallizes the vias 1126, 1132, 1134, and 1138. In one exemplary technique, the manufacturer first places the device in a low pressure, or vacuum, environment, disposes metal over the vias 1126, 1132, 1134, and 1138, heats the device 1100, and allows at least some of the metal to flow (by, for example, capillary action) into the vias 1126, 1132, 1134, and 1138, and contact the metallization layers 1122, 1158, or 1159 as the case may be. The metal may be any conductive material. For example, in certain embodiments, the material includes indium, copper, platinum, gold, silver, and/or alloys thereof. After the above-described metallizing, certain portions of the interconnects 1124, 1128, 1130, and 1136 lie above the upper surface 1105a of the encapsulating layer 1105 in order to electrically contact other metallization layers, such as the depicted metallization layers 1180 for interconnects 1128 and 1130 or the metallization layer 1182 for the interconnects 1136, 1140, and 1144. The portions of the interconnects lying above the upper surface 1105a may also electrically contact other interconnects yet to be formed, such as interconnect 1168.

[0076] As mentioned above, the manufacturer forms the layers 1104, 1106, 1108, and 1110 sequentially. After forming the layer 1104, the manufacturer uses similar processes to form layer 1106. More particularly, the manufacturer deposits and patterns the metallization layers 1180 and 1182 over the encapsulating layer 1105. After depositing the metallization layer 1122, the manufacturer arranges and affixes the first second set of components 1114 and 1115 via adhesive layers 1172 and 1174 (step 1314). As was the case with layer 1104, the manufacturer may optionally deposit a thin film dielectric layer (not shown) over the metallization layers 1180 and 1182 to insulate the metallization layers 1180 and 1182 from the components 1114 and 1115. In the depicted embodiment, the adhesive bonding layers 1172 and 1174 are disposed between the metallization layers 1180 and 1182 and the components 1114 and 1115. In one exemplary technique, the manufacturer applies the adhesive layers 1172 and 1174 directly over the encapsulating layer 1105 and/or the metallization layers 1180 and 1182, and then aligns and presses the components 1114 and 1115 to affix the components 1114 and 1115 to the adhesive layers 1172 and 1174. The adhesive layers 1172 and 1174 may be disposed such that the metallization layer 1122 electrically contacts the components 1114 and 1115.

[0077] The manufacturer then deposits and optionally patterns metallization layers 1202 and 1204, disposes the second encapsulating layer 1107 (step 1316) over and laterally between the components 1114 and 1115, soft bakes the encapsulating layer 1107, planarizes the encapsulating layer 1107, and hard bakes the encapsulating layer 1107, and forms interconnects 1168, 1206, 1208, 1210, 1212, and 1214 using similar techniques to those described in connection with layer 1104.

[0078] The components 1112-1119 may have edges that form angular interfaces with the encapsulant. By way of example, component 1115 has edge 1115a that forms an angular interface with encapsulating layer 1107. This angular interface can stress and possibly crack the encapsulating layer 1107. In certain embodiments, the manufacturer selectively removes a portion 1199 of the encapsulating layer 1107 in order to remove the encapsulating layer around this angular interface. The manufacturer may leave the portion 1199 as an empty via, or fill it with a compliant material.

[0079] In certain configurations, the multi-component substrate 1102 is sacrificial, and in an optional final step, the manufacturer removes the multi-component substrate 1102. In one such exemplary technique, the multi-component substrate 1102 is dissolved. Additionally, it is noted that although device 1100 includes four layers 1104, 1106, 1108, and 1110, the manufacturer can include as many or as few layers as desired.

[0080] As mentioned above, the components 1112-1119 can comprise a variety of subsystem components that serve a variety of functions. The components 1112-1119 may be predefined, in that they are individually fabricated before they are arranged within the device 1100. The components 1112-1119 may include integrated circuit devices. The integrated circuit devices may be digital integrated circuit devices or analog integrated circuit devices.

[0081] In certain implementations, the components 1112-1119 include components for communication, such as wireless communication or optical communication. The components may include radio frequency transmitters and/or radio frequency receivers. More generally, they may include radio frequency integrated circuits, or microwave integrated circuits. Additionally, or alternatively, the components may include optical signal processors including optical signal transmitters, such as light emitting diodes (LEDs), tunable diodes, or lasers, and optical signal receivers, such as photodiodes. Other components and structures for routing optical signals will be discussed in more detail below.

[0082] In certain embodiments, the components include sensors, such as mechanical sensors, thermal sensors, optical sensors, electrical sensors, and/or chemical sensors. As will be discussed in more detail below, the chemical sensors may be in fluid communication with external fluid samples via microfluidic channels for chemical sensing and analysis. Other exemplary sensors include accelerometers, tilt sensors, and gyroscopes.

[0083] The components may include transducers, such as actuators. Exemplary actuators include mechanical actuators, thermal actuators, optical actuators, electrical actuators, chemical actuators, and fluidic actuators. The transducers may also include motors, pistons, relays, microphones, piezoelectric devices, batteries, and/or fuel cells.

[0084] Although many of the possible component types mentioned above are active components, they may also be passive components. For example, the components may include inductors, capacitors, and/or resistors.

[0085] FIG. 15 shows a close-up view a second portion of the device 1100 of FIG. 12, and in particular shows microfluidic features for heat dissipation and for environmental sampling according to an illustrative embodiment of the invention. More particularly, the depicted component 1117 generates heat and must be cooled to prevent overheating. The metallization layer 1184 couples to the component 1117, and a microfluidic heat dissipation channel 1160 is filled with gas or liquid and thermally couples the metallization layer 1184 to ambient air generally indicated at 1186. The heat dissipation channel 1160 draws heat away from the component 1117 and towards the ambient air 1186 by convection. In alternative embodiments, the microfluidic channel draws heat to a heat reservoir (not shown) or draws heat towards other components of the device 1100 that may require higher operating temperatures.

[0086] The microfluidic channel 1160 can be patterned into the encapsulating layers 1109 and 1111 using any of the